

MGA-545P8

50 MHz to 7 GHz Medium Power Amplifier



Data Sheet

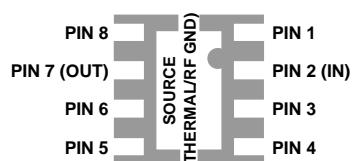
Description

Avago's MGA-545P8 is an economical, low current, medium power, easy-to-use GaAs MMIC amplifier that offers excellent power output at 5.8 GHz. Although optimized for 5.8 GHz applications, the MGA-545P8 is suitable for other applications in the 50 MHz to 7 GHz frequency range.

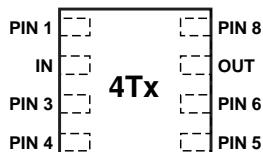
With the addition of a simple input match, the MGA-545P8 offers a small signal gain of 11.5 dB, a saturated power output of 22 dBm and a saturated gain of 9.5 dB at 5.8 GHz. The MGA-545P8 has a nominal current consumption of 92 mA in saturated mode and 135 mA in linear mode at a device voltage of 3.3 V with power added efficiency of 46% in saturated mode.

The MGA-545P8 is housed in the 2X2 mm-8L LPCC package. This package offers good thermal dissipation and very good high frequency characteristics making it appropriate for medium power applications through 7 GHz.

Pin Connections and Package Marking



BOTTOM VIEW



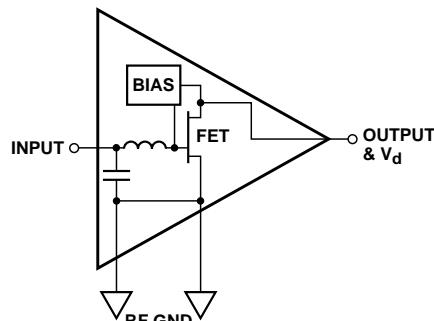
TOP VIEW

Note: Package marking provides orientation and identification.

"4T" = Device Code

"x" = Date code indicates the month of manufacture.

Simplified Schematic



Notes:

1. Enhancement mode technology employs a single positive V_{gs} , eliminating the need of negative gate voltage associated with conventional depletion mode devices.
2. Refer to reliability datasheet for detailed M TTF data.
3. Conform to JEDEC reference outline M O229 for DRP-N.



Attention: Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model (Class A), ESD Human Body Model (Class 1A)

Refer to Avago Application Note A004R: *Electrostatic Discharge, Damage and Control*.

M GA-545P8 Absolute Maximum Ratings^[1]

Parameter	Units	Absolute Maximum
V _d	V	5.0
P _{in}	dBm	20
θ _{jc}	°C/W	124
P _{diss}	W	0.8
T _j	°C	150
T _{STG}	°C	-65 to 150

Notes:

1. Operation of this device in excess of any of these limits may cause permanent damage.
2. Thermal resistance measured using 150°C Liquid Crystal Measurement Technique.
3. Board (package belly) temperature T_b is 25°C. Derate 8 mW/°C for T_b > 51°C.

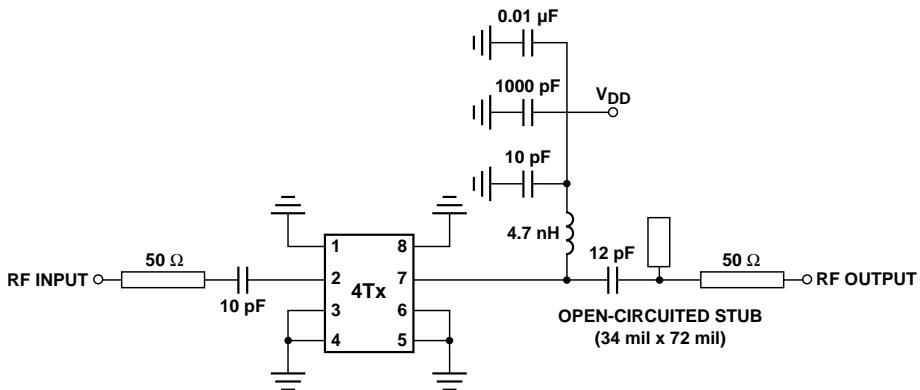


Figure 1. Production test circuit.

This circuit represents a match for maximum gain and saturated power.

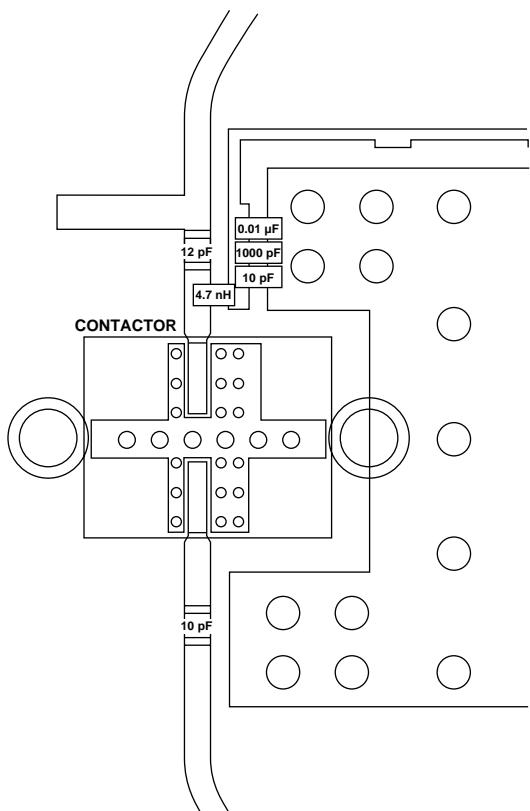


Figure 2. Close-up of production test board. Rogers 4350 Er = 3.48 ± 0.05, thickness = 10 mils.

M GA-545P8 Electrical Specifications

T_c = 25°C, V_d = 3.3 V, unless otherwise noted

Symbol	Parameter and Test Condition		Units	Min.	Typ.	Max.
Gtest_sat	Gain in test circuit at saturation <i>For all frequencies refer to note [3] unless noted otherwise</i>	f = 1.0 GHz	dB	20.0		
		f = 2.0 GHz		16.3		
		f = 3.0 GHz		13.4		
		f = 4.0 GHz		11.6		
		f = 5.0 GHz		10.05		
		f = 5.825 GHz ^[1]	8.5	9.5	10.5	
		f = 6.0 GHz		8.7		
Gtest_ss	Gain in test circuit at small signal <i>For all frequencies refer to note [3] unless noted otherwise</i>	f = 1.0 GHz	dB	22.4		
		f = 2.0 GHz		18.6		
		f = 3.0 GHz		15.9		
		f = 4.0 GHz		13.5		
		f = 5.0 GHz		12		
		f = 5.825 GHz ^[1]	10.5	11.5	13.8	
		f = 6.0 GHz		11.3		
Psat	Pout at 2.5 dB gain compression	f = 5.825 GHz ^[1]	dBm	21.5	22	–
Ids_sat	Drain Current at saturation	f = 5.825 GHz ^[1]	mA	80	92	115
Idss	Drain Current at small signal	f = 5.825 GHz ^[1]	mA	110	127	145
P1dB	Output Power at 1 dB compression point <i>For all frequencies refer to note [3] unless noted otherwise</i>	f = 1.0 GHz	dBm	21.5		
		f = 2.0 GHz		21.7		
		f = 3.0 GHz		21.3		
		f = 4.0 GHz		21.8		
		f = 5.0 GHz		21.2		
		f = 5.825 GHz ^[2]		21.0		
		f = 6.0 GHz		20.6		
PAE	Power Added Efficiency at Psat ^[4] <i>For all frequencies refer to note [3] unless noted otherwise</i>	f = 1.0 GHz	%	46.3		
		f = 2.0 GHz		46.0		
		f = 3.0 GHz		48		
		f = 4.0 GHz		44		
		f = 5.0 GHz		45		
		f = 5.825 GHz ^[1]	40	46		
		f = 6.0 GHz		47		
OIP3	Output Third Order Intercept Point [2.7 V]	f = 5.725 GHz ^[1]	dBm	31	34	–
EVM	Error Vector Magnitude Pout = 16 dBm; 54 Mbps data rate	f = 5.725 GHz ^[2]	%		5.6	
NF	Noise Figure <i>For all frequencies refer to note [3] unless noted otherwise.</i>	f = 1.0 GHz	dB	2.6		
		f = 2.0 GHz		2.7		
		f = 3.0 GHz		2.9		
		f = 4.0 GHz		3.3		
		f = 5.0 GHz		3.6		
		f = 5.825 GHz ^[2]		4.4		
		f = 6.0 GHz		5.2		

Notes:

- Measurements made on a fixed tuned production test board (figure 1), which was optimized for gain and saturated power. Excess circuit losses had been de-embedded from actual measurement. Typical data based on at least 500 parts sample size from 3 wafer lots. Future wafers allocated to this product may have nominal values anywhere within the upper and lower spec limits.
- Measurement was taken on demo board at which it was tuned for maximum gain and saturated power. Refer to application note.
- Measurement was done in a 50 Ω microstrip line, which was tuned for maximum gain and saturated power for each frequency with external double stub tuners.
- Power Added Efficiency at Psat is calculated using the following formula: $\eta_{pa} = \frac{Pout - Pin}{Vdd \times Id}$
 Pout = Psat in watts
 Pin = Input drive power in watts
 Vdd = 3.3 V
 Id = Ids_sat in Ampere

M GA-545P8 Typical Performance, $T_c = 25^\circ\text{C}$, $V_d = 3.3 \text{ V}$ unless stated otherwise.

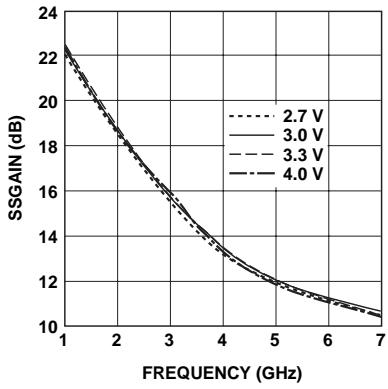


Figure 3. Small signal gain vs. frequency and voltage^[1,5].

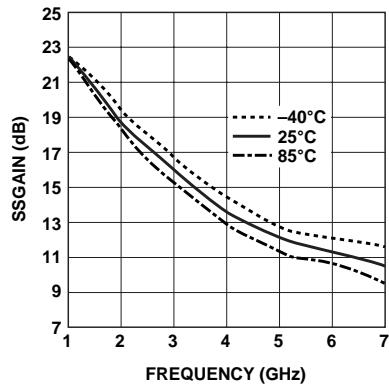


Figure 4. Small signal gain vs. frequency and temperature^[1,5].

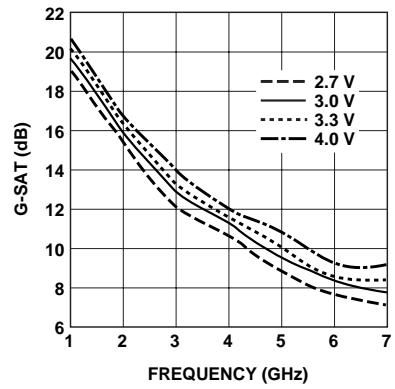


Figure 5. Saturated gain vs. frequency and voltage^[2,3,5].

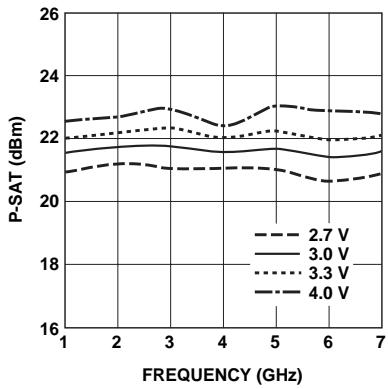


Figure 6. Saturated power vs. frequency and voltage^[2,3,5].

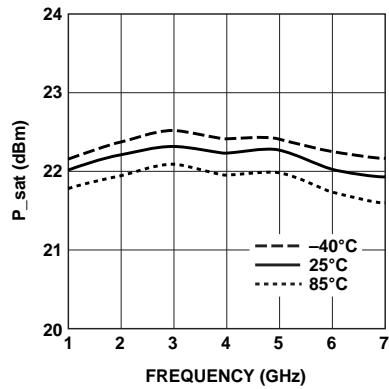


Figure 7. Saturated power vs. frequency and temperature^[2,3,5].

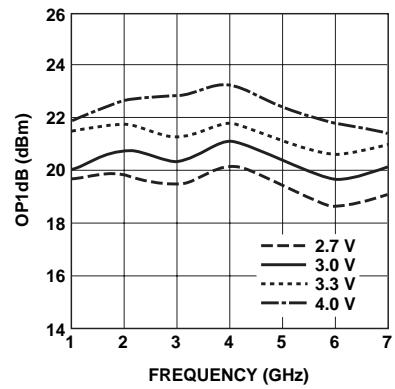


Figure 8. Output power at 1 dB gain compression vs. frequency and voltage^[2,5].

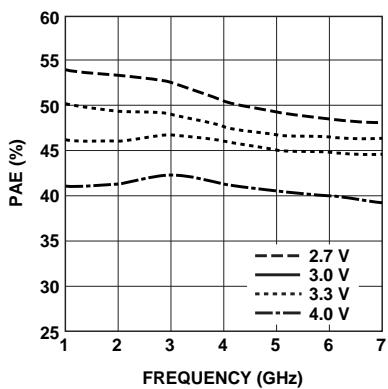


Figure 9. Power added efficiency vs. frequency and voltage^[2,3,5].

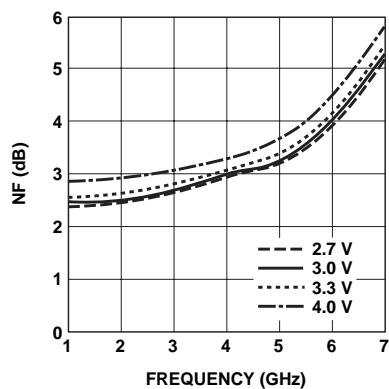


Figure 10. Noise figure vs. frequency and voltage^[2,5].

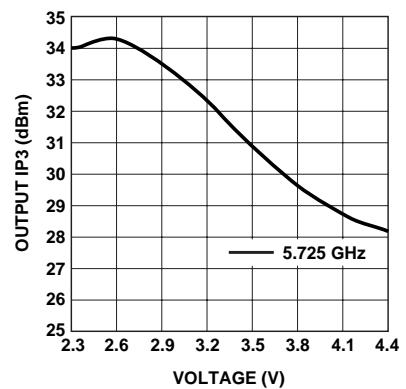


Figure 11. OIP3 vs. voltage at 5.725 GHz^[4,5].

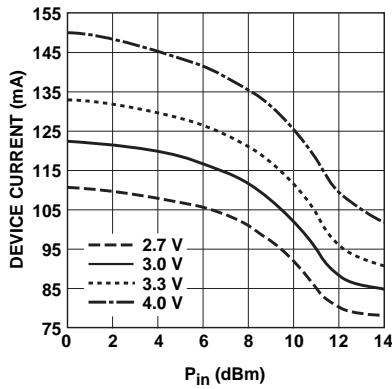


Figure 12. Device current vs. P_{in} and voltage^[4,5].

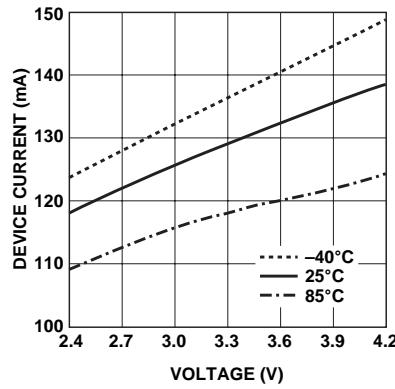


Figure 13. I_d vs. voltage and temperature (no RFdrive).

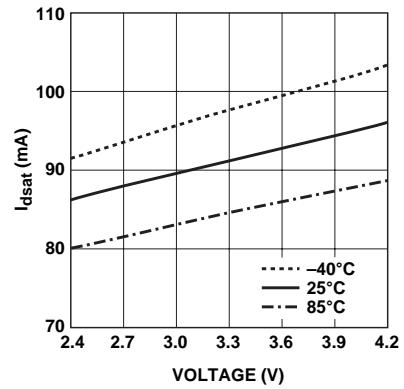


Figure 14. Saturated I_d vs. voltage and temperature^[3,4].

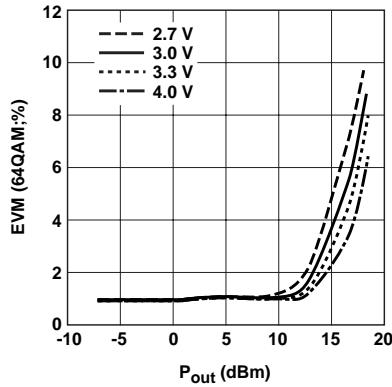


Figure 15. EVM (64QAM) vs. P_{out} and voltage at 5.725 GHz^[4].

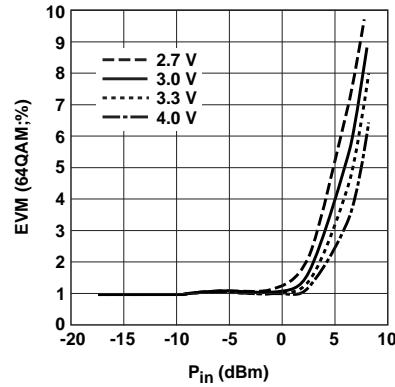


Figure 16. EVM (64QAM) vs. P_{in} and voltage at 5.725 GHz^[4].

Notes:

1. Measurement was done in a $50\ \Omega$ microstrip line with input and output tuned for maximum gain using double stub-tuners.
2. Measurement was done in a $50\ \Omega$ microstrip line with input tuned for gain and output tuned for maximum P_{sat} using double-stub tuners.
3. Measured at 2.5 dB gain compression.
4. Measurement at 5.825 GHz were made on a fixed tuned demo board that was tuned for maximum saturated output power and maximum gain.
5. Circuit losses have been de-embedded from actual measurement.

M GA-545P8 Typical Scattering Parameters

T_c = 25°C, V_d = 3.3 V, Z_o = 50 Ω

Freq.	S11		S21			S12			S22		K
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	Factor
0.05	0.08	-144.5	24.4	16.57	174.5	-32.0	0.025	0.3	0.04	6.5	1.40
0.1	0.11	-140.5	24.3	16.33	169.7	-31.9	0.025	0.0	0.04	3.9	1.40
0.2	0.17	-132.4	24.0	15.85	160.1	-31.9	0.025	-0.7	0.04	-1.4	1.40
0.3	0.25	-133.4	23.7	15.34	151.5	-31.9	0.026	-0.6	0.04	-2.7	1.39
0.4	0.30	-137.1	23.3	14.65	144.1	-31.9	0.025	1.0	0.04	-4.6	1.40
0.5	0.35	-139.0	22.9	13.96	136.5	-31.8	0.026	2.4	0.06	-10.5	1.40
0.6	0.40	-144.4	22.4	13.26	131.2	-31.8	0.026	3.7	0.07	-13.2	1.38
0.7	0.44	-149.7	21.9	12.51	124.6	-31.8	0.026	4.7	0.07	-17.5	1.39
0.8	0.47	-153.9	21.4	11.80	119.2	-31.6	0.026	5.8	0.07	-22.9	1.38
0.9	0.50	-158.5	20.9	11.11	113.9	-31.6	0.026	7.2	0.07	-28.3	1.40
1.0	0.52	-162.8	20.4	10.51	109.3	-31.4	0.027	7.8	0.08	-31.7	1.40
1.5	0.59	179.0	18.2	8.09	89.5	-30.6	0.029	13.2	0.10	-48.5	1.42
1.9	0.61	166.5	16.7	6.81	78.0	-29.9	0.032	15.6	0.11	-60.5	1.45
2.0	0.62	163.8	16.2	6.47	75.8	-29.7	0.033	16.2	0.11	-67.5	1.49
2.4	0.61	153.8	14.9	5.58	65.4	-28.9	0.036	18.2	0.12	-73.8	1.56
3.0	0.62	139.3	13.5	4.71	53.0	-27.6	0.042	17.6	0.14	-74.6	1.54
4.0	0.54	116.5	11.9	3.95	28.6	-25.5	0.053	10.8	0.19	-89.2	1.63
5.0	0.38	87.9	11.4	3.70	0.5	-23.5	0.067	-6.5	0.23	-98.4	1.68
5.1	0.34	83.6	11.3	3.67	-3.4	-23.4	0.068	-9.5	0.24	-99.5	1.71
5.2	0.30	79.2	11.3	3.66	-7.2	-23.3	0.069	-12.3	0.25	-100.6	1.75
5.3	0.26	75.1	11.2	3.62	-11.1	-23.2	0.069	-16.3	0.26	-101.8	1.80
5.4	0.21	70.9	11.1	3.61	-15.5	-23.1	0.070	-18.8	0.27	-103.9	1.83
5.5	0.15	71.0	11.1	3.59	-19.6	-23.1	0.070	-22.9	0.28	-106.9	1.88
5.6	0.11	82.8	10.9	3.53	-23.0	-23.0	0.071	-25.6	0.29	-108.7	1.91
5.7	0.08	99.7	10.9	3.51	-26.0	-22.9	0.072	-27.7	0.29	-109.9	1.91
5.8	0.06	115.1	10.9	3.49	-29.2	-22.8	0.073	-30.4	0.30	-108.9	1.91
5.9	0.06	161.8	10.8	3.48	-33.2	-22.9	0.072	-33.4	0.34	-109.1	1.90
6.0	0.10	-161.5	10.8	3.46	-39.1	-23.0	0.071	-38.4	0.36	-118.8	1.91
6.5	0.43	-166.1	9.7	3.05	-71.8	-25.4	0.054	-70.7	0.47	-136.8	2.20
7.0	0.69	165.0	6.2	2.05	-104.8	-32.3	0.024	-106.7	0.50	-157.6	4.22
8.0	0.87	117.4	-3.7	0.66	-149.2	-33.2	0.022	55.7	0.46	172.0	6.38
9.0	0.91	97.6	-19.0	0.11	-172.2	-26.8	0.046	38.8	0.42	156.3	13.14
10.0	0.93	77.7	-19.3	0.11	-6.4	-23.9	0.064	18.8	0.41	143.1	8.26
11.0	0.90	63.6	-14.1	0.20	-20.6	-22.9	0.072	8.2	0.40	129.3	5.90
12.0	0.95	50.7	-12.1	0.25	-38.3	-21.8	0.081	-5.1	0.42	117.2	2.17
13.0	0.96	41.1	-12.2	0.25	-54.0	-21.4	0.085	-15.7	0.46	102.6	1.72
14.0	0.93	30.7	-12.4	0.24	-59.4	-21.1	0.088	-25.2	0.49	87.6	3.00
15.0	0.91	27.9	-13.1	0.22	-66.6	-20.6	0.093	-29.4	0.53	80.2	3.56
16.0	0.96	22.0	-12.9	0.23	-79.5	-20.4	0.096	-40.0	0.57	70.3	1.74
17.0	0.95	14.4	-13.6	0.21	-88.3	-19.8	0.103	-44.6	0.61	62.9	1.84
18.0	0.96	8.0	-13.6	0.21	-88.0	-19.1	0.111	-56.1	0.62	50.3	1.55

M GA-545P8 Typical Noise Parameters at $T_c = 25^\circ\text{C}$, $V_d = 3.3 \text{ V}$

Frequency GHz	Fmin dB	Gopt			$R_n / 50\Omega$
		Mag	Ang		
1.0	2.1	0.46	-144	0.15	
2.0	2.4	0.44	-133	0.20	
3.0	2.5	0.44	-123	0.27	
4.0	2.9	0.39	-100	0.43	
5.0	3.2	0.26	-77	0.51	
6.0	3.5	0.13	-77	0.48	
7.0	4.4	0.38	-158	0.28	

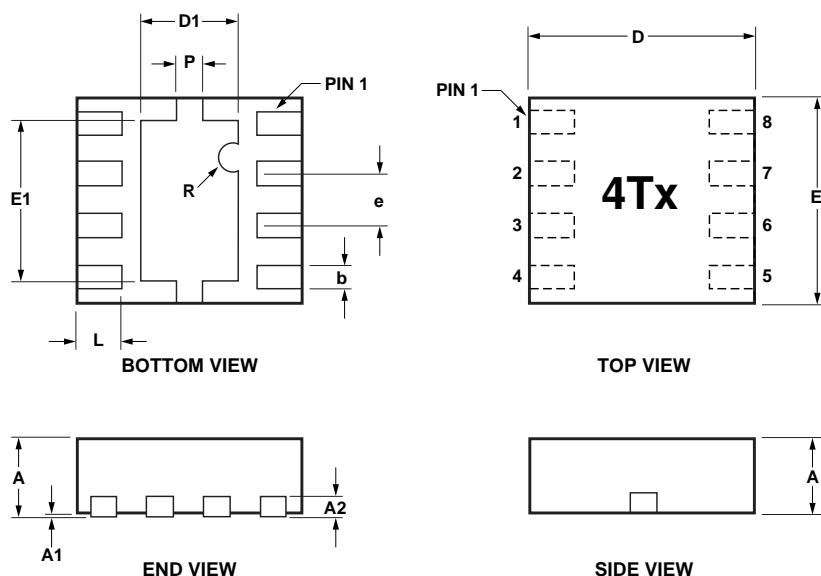
Device Models

Refer to Avago's Web Site
www.Avago.com/view/rf

Ordering Information

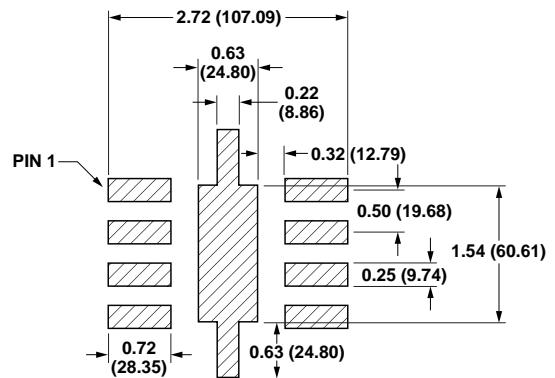
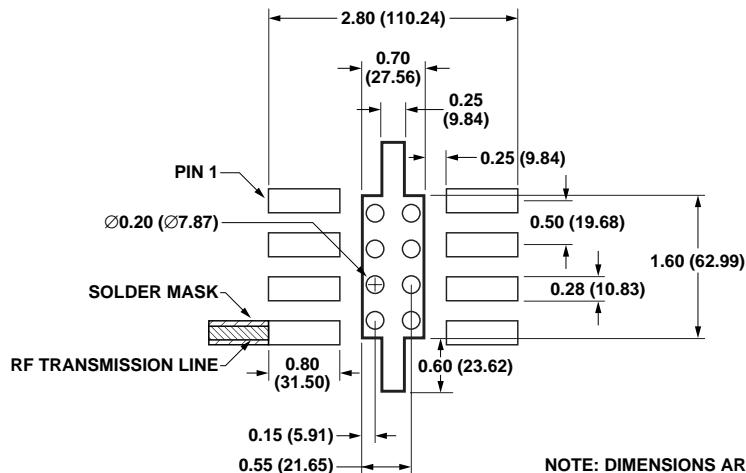
Part Number	No. of Devices	Container
MGA-545P8-TR1	3000	7" Reel
MGA-545P8-TR2	10000	13" Reel
MGA-545P8-BLK	100	Antistatic Bag

2x2 LPCC (JEDEC DFP_N) Package Dimensions

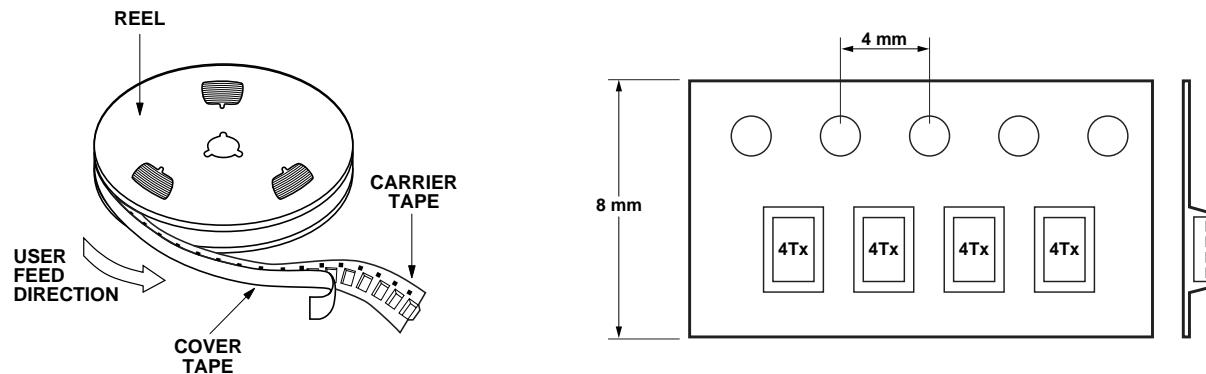


SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	0.7	0.75	0.8
A1	0	0.02	0.05
A2		0.203 REF	
b	0.225	0.25	0.275
D	1.9	2	2.1
D1	0.65	0.8	0.95
E	1.9	2	2.1
E1	1.45	1.6	1.75
e		0.50 BSC	
P	0.20	0.25	0.30
L	0.35	0.40	0.45

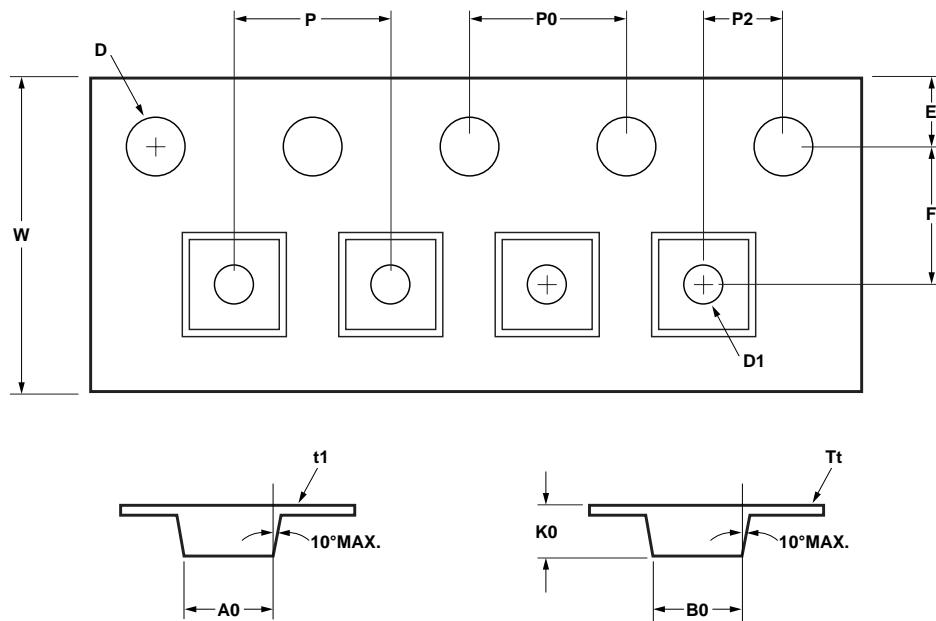
PCB Land Pattern and Stencil Design



Device Orientation



Tape Dimensions



DESCRIPTION		SYMBOL	SIZE (mm)	SIZE (INCH)
CAVITY	LENGTH	A_0	2.30 ± 0.05	0.091 ± 0.004
	WIDTH	B_0	2.30 ± 0.05	0.091 ± 0.004
	DEPTH	K_0	1.00 ± 0.05	0.039 ± 0.002
	PITCH	P	4.00 ± 0.10	0.157 ± 0.004
	BOTTOM HOLE DIAMETER	D_1	1.00 ± 0.25	0.039 ± 0.002
PERFORATION	DIAMETER	D	1.50 ± 0.10	0.060 ± 0.004
	PITCH	P_0	4.00 ± 0.10	0.157 ± 0.004
	POSITION	E	1.75 ± 0.10	0.069 ± 0.004
CARRIER TAPE	WIDTH	w	$8.00 + 0.30$ $8.00 - 0.10$	0.315 ± 0.012 0.315 ± 0.004
	THICKNESS	t_1	0.254 ± 0.02	0.010 ± 0.0008
COVER TAPE	WIDTH	C	5.4 ± 0.10	0.205 ± 0.004
	TAPE THICKNESS	T_t	0.062 ± 0.001	0.0025 ± 0.0004
DISTANCE	CAVITY TO PERFORATION (WIDTH DIRECTION)	F	3.50 ± 0.05	0.138 ± 0.002
	CAVITY TO PERFORATION (LENGTH DIRECTION)	P_2	2.00 ± 0.05	0.079 ± 0.002

For product information and a complete list of distributors, please go to our website: www.avagotech.com

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